ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Test Condition		Min	Тур	Max	Units
OFF CHARACTERISTICS	•	•					1
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_D = 0$	–250 μΑ	-60	-74		V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J				-64		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = -60 V	T _J = 25°C			-1.0	μΑ
			T _J = 150°C			-10	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V				±100	nA
ON CHARACTERISTICS (Note 3)							
Gate Threshold Voltage	V _{GS(TH)}	$V_{GS} = V_{DS}, I_D = -250 \mu A$		-1.0	-1.5	-2.0	V
Gate Threshold Temperature Coefficient	V _{GS(TH)} /T _J				3.1		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	$V_{GS} = -5.0 \text{ V}, I_D = -7.5 \text{ A}$			0.130	0.150	Ω
		V _{GS} = -5.0 V, I _D = -15 A			0.143		1
Forward Transconductance	9FS	$V_{DS} = -10 \text{ V}, I_D$	= -7.5 A		11		S
Drain-to-Source On-Voltage	V _{DS(on)}	V _{GS} = -5.0 V,	T _J = 25°C			-1.2	V
		I _D = -7.5 A	T _J = 150°C			-1.9	1
CHARGES AND CAPACITANCES	•	•					1
Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1 MHz, V _{DS} = -25 V			740	1190	pF
Output Capacitance	C _{OSS}				207	300	1
Reverse Transfer Capacitance	C _{RSS}				66	120	1
Total Gate Charge	Q _{G(TOT)}	$V_{GS} = -5.0 \text{ V}, V_{DS} = -48 \text{ V},$ $I_{D} = -18 \text{ A}$			15	26	nC
Gate-to-Source Charge	Q _{GS}				4.0		1
Gate-to-Drain Charge	Q_{GD}				7.0		1
SWITCHING CHARACTERISTICS (Note 4)	•					
Turn-On Delay Time	t _{d(ON)}				11	20	ns
Rise Time	t _r	VG9 = -5.0 V. Vni	n = -30 V.		90	180	1
Turn-Off Delay Time	t _{d(OFF)}	$V_{GS} = -5.0 \text{ V}, V_{DD} = -30 \text{ V}, \\ I_{D} = -15 \text{ A}, R_{G} = 9.1 \Omega$			28	50	1
Fall Time	t _f				70	135	1
DRAIN-SOURCE DIODE CHARACTERIS	TICS	•					
Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = -15 A	T _J = 25°C		1.5	2.5	V
			T _J = 150°C		1.3		1
Reverse Recovery Time	t _{RR}	$V_{GS} = 0 \text{ V, } d_{IS}/d_t = 100 \text{ A}/\mu\text{s,}$ $I_S = -12 \text{ A}$			60		ns
Charge Time	t _a				39		1
Discharge Time	t _b				21		1
Reverse Recovery Charge	Q _{RR}				0.13		nC

- 3. Pulse Test: pulse width $\leq 300~\mu s$, duty cycle $\leq 2\%$ 4. Switching characteristics are independent of operating junction temperatures

TYPICAL PERFORMANCE CURVES

(T_J = 25°C unless otherwise noted)

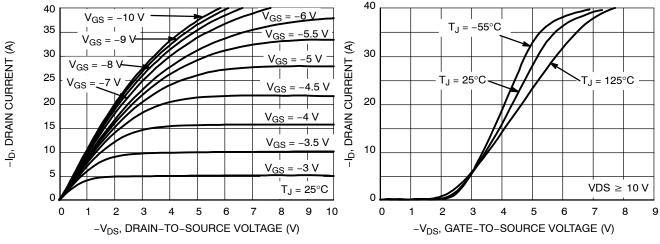


Figure 1. On-Region Characteristics

Figure 2. Transfer Characteristics

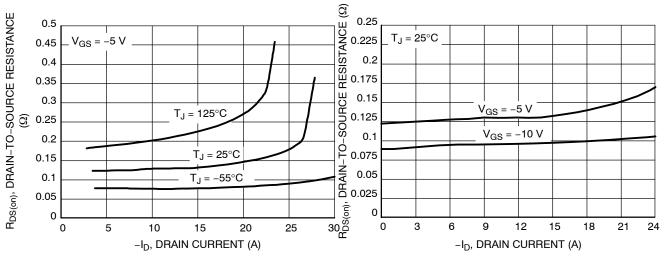


Figure 3. On-Resistance versus Drain Current and Temperature

Figure 4. On-Resistance versus Drain Current and Gate Voltage

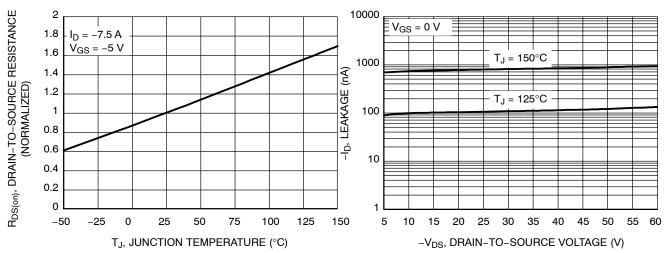


Figure 5. On–Resistance Variation with Temperature

Figure 6. Drain-to-Source Leakage Current versus Voltage

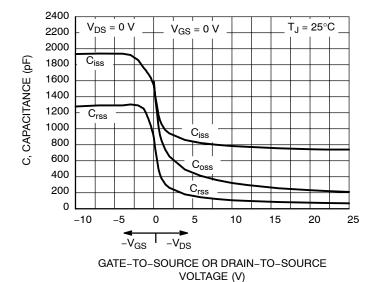


Figure 7. Capacitance Variation

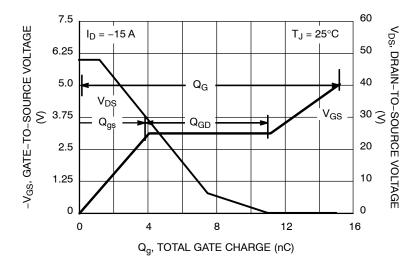
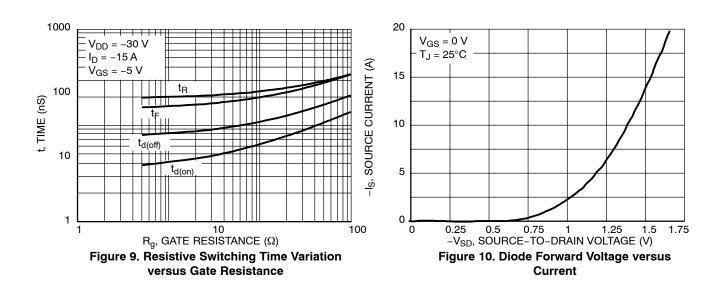


Figure 8. Gate-to-Source and Drain-to-Source Voltage versus Total Charge



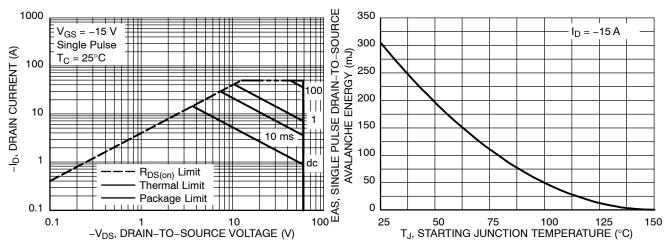


Figure 11. Maximum Rated Forward Biased Safe Operating Area

Figure 12. Maximum Avalanche Energy versus **Starting Junction Temperature**

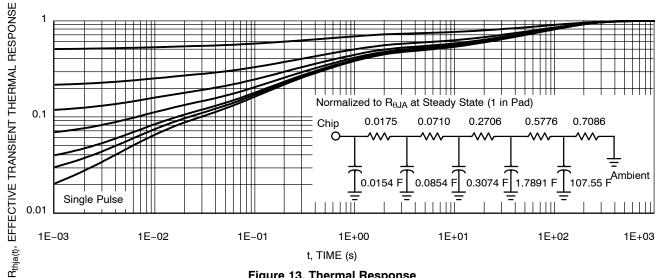


Figure 13. Thermal Response

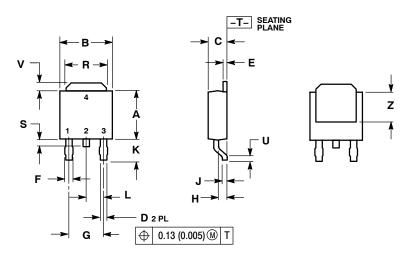
ORDERING INFORMATION

Device	Package	Shipping [†]		
NTD20P06L-1		75 Units / Rail		
NTD20P06L	DPAK	75 Units / Rail		
NTD20P06LT4		2500 /Tape & Reel		
NTD20P06L-1G		75 Units / Rail		
NTD20P06LG	DPAK (Pb-Free)	75 Units / Rail		
NTD20P06LT4G	,	2500 / Tape & Reel		

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

DPAK-3 CASE 369C-01 ISSUE O



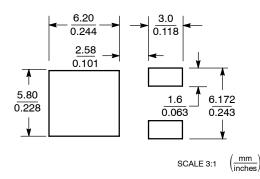
NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.235	0.245	5.97	6.22	
В	0.250	0.265	6.35	6.73	
С	0.086	0.094	2.19	2.38	
D	0.027	0.035	0.69	0.88	
E	0.018	0.023	0.46	0.58	
F	0.037	0.045	0.94	1.14	
G	0.180 BSC		4.58 BSC		
Н	0.034	0.040	0.87	1.01	
J	0.018	0.023	0.46	0.58	
K	0.102	0.114	2.60	2.89	
L	0.090 BSC		2.29 BSC		
R	0.180	0.215	4.57	5.45	
S	0.025	0.040	0.63	1.01	
U	0.020		0.51		
V	0.035	0.050	0.89	1.27	
Z	0.155		3.93		

STYLE 2: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN

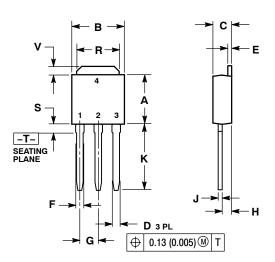
SOLDERING FOOTPRINT*

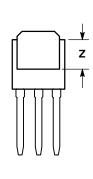


*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

DPAK-3 CASE 369D-01 ISSUE B





NOTES:

- DIMENSIONING AND TOLERANCING PER
 ANSI V14 5M 1982
- ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.235	0.245	5.97	6.35	
В	0.250	0.265	6.35	6.73	
С	0.086	0.094	2.19	2.38	
D	0.027	0.035	0.69	0.88	
Е	0.018	0.023	0.46	0.58	
F	0.037	0.045	0.94	1.14	
G	0.090 BSC		2.29 BSC		
Н	0.034	0.040	0.87	1.01	
J	0.018	0.023	0.46	0.58	
Κ	0.350	0.380	8.89	9.65	
R	0.180	0.215	4.45	5.45	
S	0.025	0.040	0.63	1.01	
٧	0.035	0.050	0.89	1.27	
Z	0.155		3.93		

STYLE 2: PIN 1. GATE

- 2. DRAIN
- 3. SOURCE
- 4. DRAIN

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